### BTA204 series D, E and F

### **GENERAL DESCRIPTION**

Passivated guaranteed commutation triacs in a plastic envelope, intended for use in motor control circuits or with other highly inductive loads. These devices balance the requirements of commutation performance and gate sensitivity. The "sensitive gate" E series and "logic level" D series are intended for interfacing with low power drivers, including micro controllers.

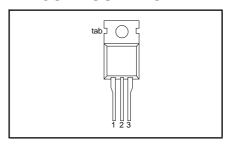
### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	MAX.	UNIT
	BTA204- BTA204- BTA204-	600D 600E 600F	- 800E	
$V_{DRM}$	Repetitive peak	600	800	V
I <sub>T(RMS)</sub> I <sub>TSM</sub>	off-state voltages RMS on-state current Non-repetitive peak on-state current	4 25	4 25	A A

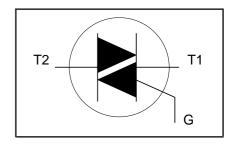
### **PINNING - TO220AB**

PIN	DESCRIPTION			
1	main terminal 1			
2	main terminal 2			
3	gate			
tab	main terminal 2			

### **PIN CONFIGURATION**



### **SYMBOL**



### **LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT
$V_{DRM}$	Repetitive peak off-state voltages		-	<b>-600</b> 600 <sup>1</sup>	<b>-800</b> 800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave;	-		4	Α
I <sub>TSM</sub>	Non-repetitive peak on-state current	$T_{mb} \le 107$ °C full sine wave; $T_j = 25$ °C prior to surge $t = 20$ ms	-		25	Ą
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t = 16.7 ms t = 10 ms	-		27 3.1	A A <sup>2</sup> s
dl <sub>⊤</sub> /dt	Repetitive rate of rise of on-state current after	$I_{TM} = 6 \text{ A}; I_G = 0.2 \text{ A};$ $dI_G/dt = 0.2 \text{ A/}\mu\text{s}$	-		00	A/μs
I <sub>GM</sub>	triggering Peak gate current		-		2	Α
P <sub>GM</sub>	Peak gate power		-		5	W
$P_{G(AV)}$	Average gate power	over any 20 ms period	-	١	).5	W
$T_{stg}^{stg}$	Storage temperature Operating junction temperature	policu	-40 -		50 25	ů

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<sup>1</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 6  $A/\mu s$ .

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### THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{\text{th j-mb}}$ $R_{\text{th j-a}}$	Thermal resistance junction to mounting base Thermal resistance junction to ambient	full cycle half cycle in free air	- - -	- - 60	3.0 3.7 -	K/W K/W K/W

### STATIC CHARACTERISTICS

 $T_i = 25$  °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.		MAX.		UNIT
		BTA204-			D	Е	F	
I <sub>GT</sub>	Gate trigger current <sup>2</sup>	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$						
		T2+ G+	-	-	5	10	25	mA
		T2+ G-	-	-	5 5	10	25	mA
		T2- G-	-	-	5	10	25	mA
l I <sub>L</sub>	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$						
		T2+ G+	-	-	6	12	20	mA
		T2+ G-	-	-	9	18	30	mA
		T2- G-	-	-	6	12	20	mΑ
I <sub>H</sub>	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	-	6	12	20	mA
$V_T$	On-state voltage	$I_{T} = 5 \text{ A}$	_	1.4		1.7		lv
V <sub>GT</sub>	Gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$	_	0.7		1.5		V
G i		$V_D^D = 400 \text{ V}; I_T = 0.1 \text{ A};$	0.25	0.4		-		V
		$T_i = 125 ^{\circ}\text{C}$						
I <sub>D</sub>	Off-state leakage current	$ \begin{vmatrix} V_D = V_{DR\%(max)}; \\ T_i = 125 \ C \end{vmatrix} $	-	0.1		0.5		mΑ
		$T_j = 125 \degree C^{-3}$						

### **DYNAMIC CHARACTERISTICS**

T<sub>i</sub> = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS		MIN.		TYP.	MAX.	UNIT
		BTA204-	D	E	F			
dV <sub>D</sub> /dt	Critical rate of rise of off-state voltage	V <sub>DM</sub> = 67% V <sub>DRM(max)</sub> ; T <sub>j</sub> = 125 °C; exponential waveform; gate open circuit	20	30	50	-	-	V/μs
dI <sub>com</sub> /dt	Critical rate of change of commutating current	$V_{DM} = 400 \text{ V}; T_j = 125 ^{\circ}\text{C};$ $I_{T_{(RMS)}} = 4 \text{ A};$ $dV_{com}/dt = 20 \text{V}/\mu\text{s}; \text{ gate}$ open circuit	1.0	2.0	2.5	-	-	A/ms
dl <sub>com</sub> /dt	Critical rate of change of commutating current	$V_{DM} = 400 \text{ V; } T_j = 125 \text{ °C;}$ $I_{T(RMS)} = 4 \text{ A;}$ $dV_{com}/dt = 0.1 \text{ V/}\mu\text{s; gate}$ open circuit	5.0	-	-	-	-	A/ms
<b>t</b> <sub>gt</sub>	Gate controlled turn-on time	$I_{TM} = 12 \text{ A}; V_D = V_{DRM(max)};$ $I_G = 0.1 \text{ A}; dI_G/dt = 5 \text{ A}/\mu s$	-	-	-	2	-	μs

<sup>2</sup> Device does not trigger in the T2-, G+ quadrant.

Philips Semiconductors Product specification

# Three quadrant triacs guaranteed commutation

### BTA204 series D, E and F

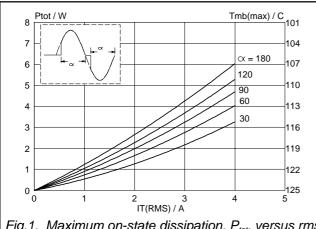


Fig.1. Maximum on-state dissipation,  $P_{tot}$ , versus rms on-state current,  $I_{T(RMS)}$ , where  $\alpha = conduction$  angle.

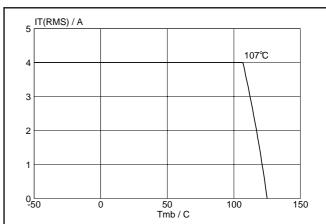


Fig.4. Maximum permissible rms current  $I_{T(RMS)}$ , versus mounting base temperature  $T_{mb}$ .

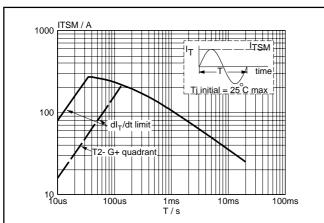


Fig.2. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus pulse width  $t_p$ , for sinusoidal currents,  $t_p \le 20$ ms.

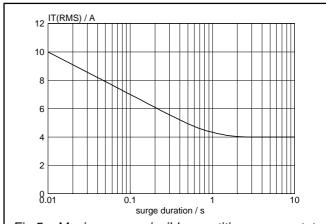


Fig.5. Maximum permissible repetitive rms on-state current  $I_{T(RMS)}$ , versus surge duration, for sinusoidal currents, f = 50 Hz;  $T_{mb} \le 107$  °C.

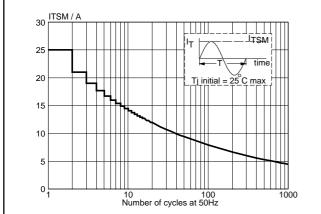


Fig.3. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus number of cycles, for sinusoidal currents, f = 50 Hz.

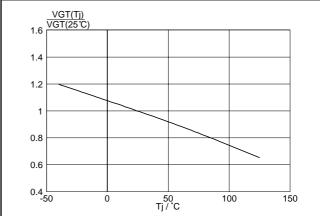
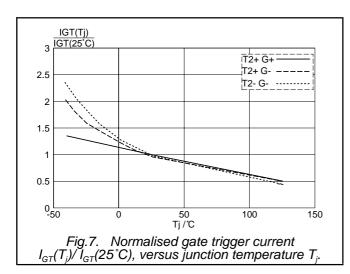
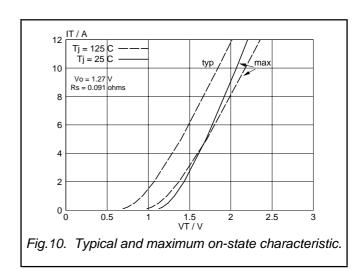
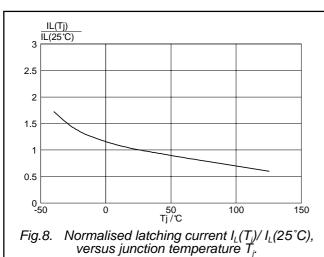


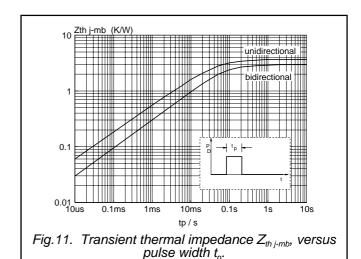
Fig.6. Normalised gate trigger voltage  $V_{GT}(T_j)/V_{GT}(25^{\circ}C)$ , versus junction temperature  $T_{j}$ .

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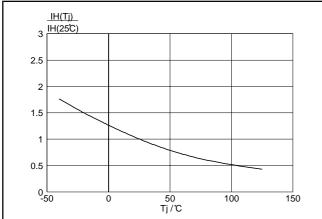
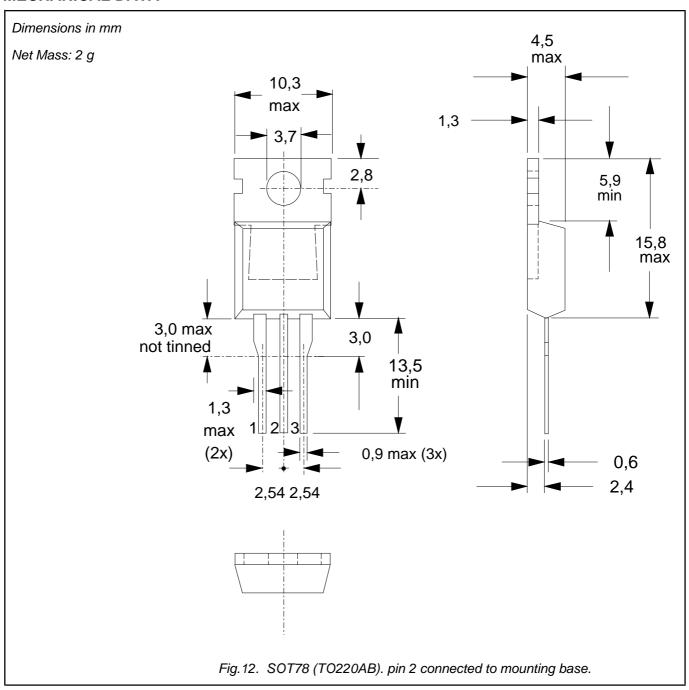


Fig.9. Normalised holding current  $I_H(T_i)/I_H(25^{\circ}\text{C})$ , versus junction temperature  $T_j$ .

### BTA204 series D, E and F

### **MECHANICAL DATA**



- Refer to mounting instructions for SOT78 (TO220) envelopes.
   Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

# Three quadrant triacs guaranteed commutation

BTA204 series D, E and F

#### **DEFINITIONS**

DATA SHEET STATUS						
DATA SHEET STATUS <sup>3</sup>	PRODUCT STATUS <sup>4</sup>	DEFINITIONS				
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice				
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product				
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A				

#### Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

#### Application information

Where application information is given, it is advisory and does not form part of the specification.

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<sup>3</sup> Please consult the most recently issued datasheet before initiating or completing a design.

**<sup>4</sup>** The product status of the device(s) described in this datasheet may have changed since this datasheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.